Abstracts

An X-Band Dual-Gate FET Up-Converter

W.C. Tsai, S.F. Paik, B.S. Hewitt, N. Gregory and P. Tanzi. "An X-Band Dual-Gate FET Up-Converter." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 495-497.

An up-converter using dual-gate GaAs FET was operated at X-band output frequencies with an IF input at 700 MHz. The FET up-converter offers advantages of conversion gain (up to 15 dB), low noise figure (3.2 dB) and built-in port-to-port isolation. The power output saturated at +9 dBm, and the third-order IM product at the 1 dB compression point was -22 dBC.

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